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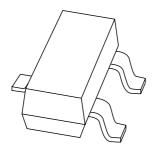
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Kind regards,

Team Nexperia

## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BSR13**; **BSR14**NPN switching transistors

Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 13



# **NPN** switching transistors

**BSR13**; **BSR14** 

#### **FEATURES**

- High current (max. 800 mA)
- Low voltage (max. 40 V).

#### **APPLICATIONS**

• Switching and linear applications.

#### **DESCRIPTION**

NPN switching transistor in a SOT23 plastic package. PNP complements: BSR15 and BSR16.

#### **MARKING**

| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| BSR13       | U7*                         |
| BSR14       | U8*                         |

#### Note

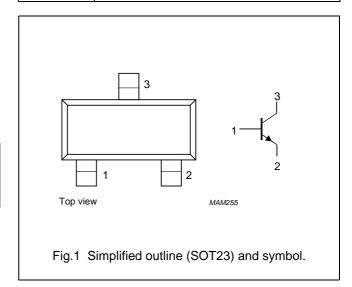
1. \* = p : Made in Hong Kong.

\* = t : Made in Malaysia.

\* = W : Made in China.

#### **PINNING**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



#### **ORDERING INFORMATION**

| TYPE   |      | PACKAGE                                  |       |  |  |  |
|--------|------|--|-------|--|--|--|
| NUMBER | NAME | DESCRIPTION VERSION                      |       |  |  |  |
| BSR13  | _    | plastic surface mounted package; 3 leads | SOT23 |  |  |  |
| BSR14  |      |  |       |  |  |  |

# NPN switching transistors

BSR13; BSR14

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS               | MIN. | MAX. | UNIT |
|------------------|-------------------------------|--------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter             |      |      |      |
|                  | BSR13                         |                          | _    | 60   | V    |
|                  | BSR14                         |                          | _    | 75   | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                |      |      |      |
|                  | BSR13                         |                          | _    | 30   | V    |
|                  | BSR14                         |                          | _    | 40   | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector           |      |      |      |
|                  | BSR13                         |                          | _    | 5    | V    |
|                  | BSR14                         |                          | _    | 6    | V    |
| I <sub>C</sub>   | collector current (DC)        |                          | _    | 800  | mA   |
| I <sub>CM</sub>  | peak collector current        |                          | _    | 800  | mA   |
| I <sub>BM</sub>  | peak base current             |                          | _    | 200  | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C | _    | 250  | mW   |
| T <sub>stg</sub> | storage temperature           |                          | -65  | +150 | °C   |
| Tj               | junction temperature          |                          | _    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                          | -65  | +150 | °C   |

#### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | note 1     | 500   | K/W  |

#### Note

#### **CHARACTERISTICS**

 $T_j$  = 25 °C unless otherwise specified.

| SYMBOL           | PARAMETER                 | CONDITIONS  | MIN. | MAX. | UNIT |
|------------------|---------------------------|---|------|------|------|
| I <sub>CBO</sub> | collector cut-off current |   |      |      |      |
|                  | BSR13                     | I <sub>E</sub> = 0; V <sub>CB</sub> = 50 V                          | _    | 30   | nA   |
|                  |                           | I <sub>E</sub> = 0; V <sub>CB</sub> = 50 V; T <sub>j</sub> = 150 °C | _    | 10   | μΑ   |
|                  | collector cut-off current |   |      |      |      |
|                  | BSR14                     | I <sub>E</sub> = 0; V <sub>CB</sub> = 60 V                          | _    | 10   | nA   |
|                  |                           | I <sub>E</sub> = 0; V <sub>CB</sub> = 60 V; T <sub>j</sub> = 150 °C | _    | 10   | μΑ   |
| I <sub>EBO</sub> | emitter cut-off current   | I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V                           |      |      |      |
|                  | BSR13                     |   | _    | 30   | nA   |
|                  | BSR14                     |   | _    | 10   | nA   |

<sup>1.</sup> Transistor mounted on an FR4 printed-circuit board.

# NPN switching transistors

BSR13; BSR14

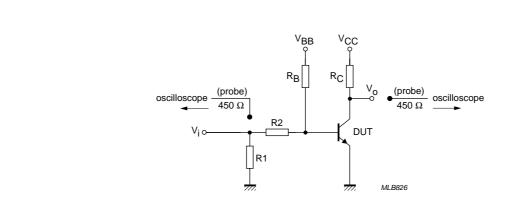
| SYMBOL             | PARAMETER                            | CONDITIONS  | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|---|------|------|------|
| h <sub>FE</sub>    | DC current gain                      | I <sub>C</sub> = 0.1 mA; V <sub>CE</sub> = 10 V; note 1         | 35   | _    |      |
|                    |                                      | I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 10 V; note 1           | 50   | _    |      |
|                    |                                      | I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; note 1          | 75   | _    |      |
|                    |                                      | I <sub>C</sub> = 150 mA; V <sub>CE</sub> = 10 V; note 1         | 100  | 300  |      |
|                    |                                      | I <sub>C</sub> = 150 mA; V <sub>CE</sub> = 1 V; note 1          | 50   | _    |      |
|                    | DC current gain                      | I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 10 V; note 1         |      |      |      |
|                    | BSR13                                |   | 30   | _    |      |
|                    | BSR14                                |   | 40   | _    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA                 |      |      |      |
|                    | BSR13                                |   | _    | 400  | mV   |
|                    | BSR14                                |   | _    | 300  | mV   |
|                    | collector-emitter saturation voltage | $I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$                     |      |      |      |
|                    | BSR13                                |   | _    | 1.6  | V    |
|                    | BSR14                                |   | _    | 1    | V    |
| V <sub>BEsat</sub> | base-emitter saturation voltage      | I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA                 |      |      |      |
|                    | BSR13                                |   | _    | 1.3  | V    |
|                    | BSR14                                |   | 0.6  | 1.2  | V    |
|                    | base-emitter saturation voltage      | $I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$                     |      |      |      |
|                    | BSR13                                |   | _    | 2.6  | V    |
|                    | BSR14                                |   | _    | 2    | V    |
| C <sub>c</sub>     | collector capacitance                | $I_E = I_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$ | _    | 8    | pF   |
| f <sub>T</sub>     | transition frequency                 | $I_C = 20 \text{ mA}; V_{CE} = 20 \text{ V};$                   |      |      |      |
|                    | BSR13                                | f = 100 MHz   | 250  | _    | MHz  |
|                    | BSR14                                |   | 300  | _    | MHz  |
| Switching t        | imes (between 10% and 90% levels     | ); see Fig.2  |      | •    | •    |
| t <sub>on</sub>    | turn-on time                         | I <sub>Con</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;            | _    | 35   | ns   |
| t <sub>d</sub>     | delay time                           | I <sub>Boff</sub> = −15 mA                                      | _    | 15   | ns   |
| t <sub>r</sub>     | rise time                            | ]   | _    | 20   | ns   |
| t <sub>off</sub>   | turn-off time                        | 1   | _    | 250  | ns   |
| t <sub>s</sub>     | storage time                         | 1   | _    | 200  | ns   |
| t <sub>f</sub>     | fall time                            | 1   | _    | 60   | ns   |

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

# NPN switching transistors

BSR13; BSR14



$$\begin{split} &V_{i}=9.5 \text{ V; T}=500 \text{ } \mu\text{s; } t_{p}=10 \text{ } \mu\text{s; } t_{f}=t_{f} \leq 3 \text{ ns.} \\ &R1=68 \text{ } \Omega; \text{ } R2=325 \text{ } \Omega; \text{ } R_{B}=325 \text{ } \Omega; \text{ } R_{C}=160 \text{ } \Omega. \\ &V_{BB}=-3.5 \text{ V; } V_{CC}=29.5 \text{ V.} \end{split}$$

Oscilloscope: input impedance  $Z_i$  =  $\geq 100~\Omega.$ 

Fig.2 Test circuit for switching times.

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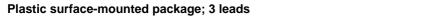
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# NPN switching transistors

BSR13; BSR14

SOT23

#### **PACKAGE OUTLINE**



-B -[A] X = v M A 3 **→** | w (M) B е detail X scale **DIMENSIONS** (mm are the original dimensions)  $A_1$ e<sub>1</sub>  $\mathbf{H}_{\mathsf{E}}$  $\mathsf{L}_\mathsf{p}$ UNIT bp Q max 0.45 0.55 0.1 0.9 0.38

| OUTLINE | REFERE |          | REFERENCES |  |            | ISSUE DATE                       |
|---------|--------|----------|------------|--|------------|----------------------------------|
| VERSION | IEC    | JEDEC    | JEITA      |  | PROJECTION | ISSUE DATE                       |
| SOT23   |        | TO-236AB |            |  |            | <del>-04-11-04</del><br>06-03-16 |

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# NPN switching transistors

**BSR13**; **BSR14** 

#### **DATA SHEET STATUS**

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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Printed in The Netherlands R75/04/pp8 Date of release: 2004 Jan 13 Document order number: 9397 750 12419



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